

Docket Number: 081468-0309022 Client Reference: P-1841.000-US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re the Application of

SASELMANS et al.

Group Art Unit: 1651

Application No.: 10/814,822

Examiner: Unassigned

Filed: April 1, 2004

Confirmation No.: 5320

For: LITHOGRAPHIC APPARATUS, DEVICE MANUFACTURING METHOD AND DEVICE

MANUFACTURED THEREBY

September 9, 2004

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. 1.56, the attention of the Patent and Trademark Office is hereby directed to the following U.S. patent application(s):

Examiner's Initials	First Inventor	Application No.	Filing Date	Enclosed					
22.	DE SMIT (081468-0309173)	10/820,227	04/08/2004	 ☑ Specification ☑ Drawings ☑ Other: stamped receipt card 					
	DE SMIT (081468-0309978)	10/860,662	06/04/2004	☒ Specification☒ Drawings☒ Other: stamped receipt card					
	DUINEVELD et al. (081468-0308101)	10/773,461	02/09/2004	 ☑ Specification ☑ Drawings ☑ Other: stamped receipt card 					
	FLAGELLO et al. (081468-0302644)	10/698,012	10/31/2003	☑ Specification☑ Drawings☑ Other: stamped receipt card					
	DE SMIT et al. (081468-0306530)	10/705,804	11/12/2003	☑ Specification☑ Drawings☑ Other: stamped receipt card					
	LOF et al. (081468-0306781)	10/705,805	11/12/2003	☑ Specification☑ Drawings☑ Other: stamped receipt card					
D.R.	LOF et al. (081468-0306524)	10/705,783	11/12/2003	☑ Specification☑ Drawings☑ Other: stamped receipt					

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Reviewed 11/2/05

DO NOT Print

Examiner's Initials	First Inventor	Application No.	Filing Date	Enclosed
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CE WINGE LIN	VAN SANTEN et al. (081468-0307331)	10/743,271	12/23/2003	☒ Specification☒ Drawings☒ Other: stamped receipt card
& TRAD MINE	MULKENS et al. (081468-0307333)	10/743,266	12/23/2003	☑ Specification☑ Drawings☑ Other: stamped receipt card
	DERKSEN et al. (081468-0306526)	10/705,785	11/12/2003	☑ Specification☑ Drawings☑ Other: stamped receipt card
	SIMON et al. (081468-0307087)	10/724,402	12/01/2003	☑ Specification☑ Drawings☑ Other: stamped receipt card
	BLEEKER (081468-0306527)	10/715,116	11/18/2003	☑ Specification☑ Drawings☑ Other: stamped receipt card
	STREEFKERK et al. (081468-0306882)	10/719,683	11/24/2003	☑ Specification☑ Drawings☑ Other: stamped receipt card
	LOF et al. (081468-0306525)	10/705,816	11/12/2003	☑ Specification☑ Drawings☑ Other: stamped receipt card
	DIERICHS (081468-0308270)	10/775,326	02/11/2004	☑ Specification☑ Drawings☑ Other: stamped receipt card
	LOF et al. (081468-0309957)	10/857,614	06/01/2004	☑ Specification☑ Drawings☑ Other: stamped receipt card
	SUWA et al. (Reissue Application of U.S. Patent No. 6,191,429 B1)	10/367,910	02/19/2003	Specification Drawings ☐ Other: stamped receipt card
\mathcal{DR}	BASELMANS et al. (081468-0309488)	10/835,856	05/03/2004	 ✓ Specification ✓ Drawings ✓ Other: stamped receipt card

*The Examiner's initials adjacent a citation indicates he/she has considered the cited application relative to the subject application.

It is respectfully requested that these applications and the art cited therein during examination be expressly considered during the prosecution of this application and be made of record in this application. The identification of the above U.S. patent applications is not to be construed as a waiver of secrecy as to those applications now or upon issuance of the present application as a patent.

<u>PLEASE DO NOT PRINT</u> the above information on the patent which results from this application.

Consideration of each listed application is earnestly solicited since unpublished patent applications are contemplated as IDS material; see the exception in Rule 98(a)(2)(iii) and note the penultimate sentence of MPEP 609.

Further, in keeping with MPEP 609, subsec. C(2), 2nd para., line 10 to end of the paragraph (especially note lines 18-25) PLEASE <u>RETURN A COPY OF THIS LETTER</u> with the Examiner's initials adjacent each above listing so that applicant will know that each listed application has been considered as required by PTO policy.

Secondly, please consider each document which is listed on the attached Form PTO-1449 and return a copy of that form with the Examiner's initials adjacent each citation, a copy of each document enclosed except for any U.S. patents and published patent applications. It is respectfully requested that these documents listed on the Form PTO-1449 be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed before the mailing date of the first Office Action on the merits in the present application. No certification or fee is required.

Respectfully Submitted,

PILLSBURY WINTHROP LLF

Jean-Paul G. Hoffinan Registration Number 42663 Customer Number: 00909

P.O. Box 10500 McLean, VA 22102

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